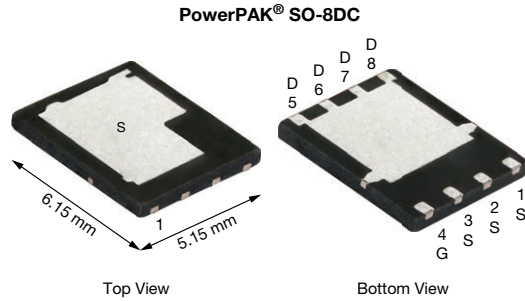


N-Channel 30 V (D-S) MOSFET



FEATURES

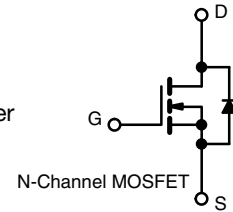
- TrenchFET® Gen IV power MOSFET
- Optimized Q_g , Q_{gd} , and Q_{gd}/Q_{gs} ratio reduces switching related power loss
- Top side cooling feature provides additional venue for thermal transfer
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Synchronous rectification
- High power density DC/DC
- Synchronous buck converter
- OR-ing
- Load switching
- Battery management



PRODUCT SUMMARY	
V_{DS} (V)	30
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10$ V	0.00080
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 4.5$ V	0.00115
Q_g typ. (nC)	48
I_D (A)	100 ^{a, g}
Configuration	Single

ORDERING INFORMATION	
Package	PowerPAK SO-8DC
Lead (Pb)-free and halogen-free	SiDR390DP-T1-GE3

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	V_{DS}	30	V	
Gate-source voltage	V_{GS}	+20 / -16	V	
Continuous drain current ($T_J = 150$ °C)	I_D	$T_C = 25$ °C	100 ^a	A
		$T_C = 70$ °C	100 ^a	
		$T_A = 25$ °C	69.9 ^{b, c}	
		$T_A = 70$ °C	55.9 ^{b, c}	
Pulsed drain current ($t = 100$ μ s)	I_{DM}	400	A	
Continuous source-drain diode current	I_S	$T_C = 25$ °C	100	A
		$T_A = 25$ °C	5.6 ^{b, c}	
Single pulse avalanche current	I_{AS}	40	A	
Single pulse avalanche energy	E_{AS}	80	mJ	
Maximum power dissipation	P_D	$T_C = 25$ °C	125	W
		$T_C = 70$ °C	80	
		$T_A = 25$ °C	6.25 ^{b, c}	
		$T_A = 70$ °C	4 ^{b, c}	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +150	°C	
Soldering recommendations (peak temperature) ^c		260	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^b	R_{thJA}	15	20	°C/W
Maximum junction-to-case (drain)	R_{thJC}	0.8	1	
Maximum junction-to-case (source)	R_{thJC}	1.1	1.4	

Notes

- Package limited
- Surface mounted on 1" x 1" FR4 board
- $t = 10$ s
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8DC is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- Maximum under steady state conditions is 54 °C/W
- $T_C = 25$ °C



SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	30	-	-	V	
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$	-	17.5	-	mV/ $^\circ\text{C}$	
$V_{GS(th)}$ temperature coefficient	$\Delta V_{GS(th)}/T_J$		-	-6.3	-		
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	0.8	-	2	V	
Gate-source leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = +20, -16\text{ V}$	-	-	± 100	nA	
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 30\text{ V}$, $V_{GS} = 0\text{ V}$	-	-	1	μA	
		$V_{DS} = 30\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 55\text{ }^\circ\text{C}$	-	-	10		
On-state drain current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}$, $V_{GS} = 10\text{ V}$	50	-	-	A	
Drain-source on-state resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 20\text{ A}$	-	0.00065	0.00080	Ω	
		$V_{GS} = 4.5\text{ V}$, $I_D = 15\text{ A}$	-	0.00090	0.00115		
Forward transconductance ^a	g_{fs}	$V_{DS} = 10\text{ V}$, $I_D = 20\text{ A}$	-	110	-	S	
Dynamic ^b							
Input capacitance	C_{ISS}	$V_{DS} = 15\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$	-	10 180	-	pF	
Output capacitance	C_{OSS}		-	3290	-		
Reverse transfer capacitance	C_{RSS}		-	306	-		
C_{RSS}/C_{ISS} ratio			-	0.031	0.062		
Total gate charge	Q_g	$V_{DS} = 15\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 20\text{ A}$	-	102	153	nC	
Gate-source charge	Q_{gs}	$V_{DS} = 15\text{ V}$, $V_{GS} = 4.5\text{ V}$, $I_D = 20\text{ A}$	-	48	72		
Gate-drain charge	Q_{gd}		-	22	-		
Output charge	Q_{oss}		-	4.7	-		
Gate resistance	R_g	$V_{DS} = 15\text{ V}$, $V_{GS} = 0\text{ V}$	-	105	-		
Turn-on delay time	$t_{d(on)}$	$f = 1\text{ MHz}$	0.5	1.3	2.5	Ω	
Rise time	t_r		$V_{DD} = 15\text{ V}$, $R_L = 0.75\text{ }\Omega$ $I_D \cong 20\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\text{ }\Omega$	-	15	30	ns
Turn-off delay time	$t_{d(off)}$			-	16	32	
Fall time	t_f			-	46	90	
Turn-on delay time	$t_{d(on)}$	-		10	20		
Rise time	t_r	-		51	100		
Turn-off delay time	$t_{d(off)}$	-		63	120		
Fall time	t_f	-		78	155		
Fall time	t_f	-		27	34		
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I_S	$T_C = 25\text{ }^\circ\text{C}$	-	-	100	A	
Pulse diode forward current ($t_p = 100\text{ }\mu\text{s}$)	I_{SM}		-	-	400		
Body diode voltage	V_{SD}	$I_S = 10\text{ A}$	-	0.68	1.1	V	
Body diode reverse recovery time	t_{rr}	$I_F = 20\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25\text{ }^\circ\text{C}$	-	68	135	ns	
Body diode reverse recovery charge	Q_{rr}		-	98	180	nC	
Reverse recovery fall time	t_a		-	29	-	ns	
Reverse recovery rise time	t_b		-	39	-		

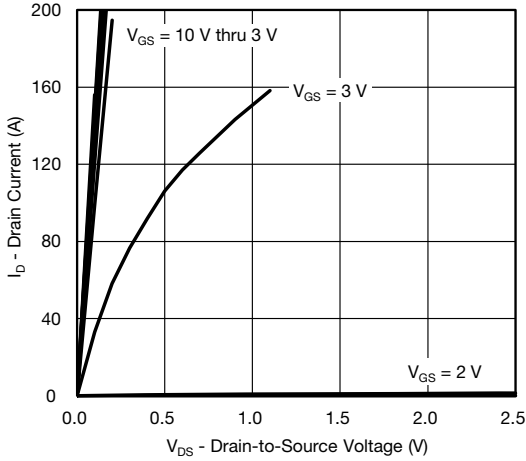
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing

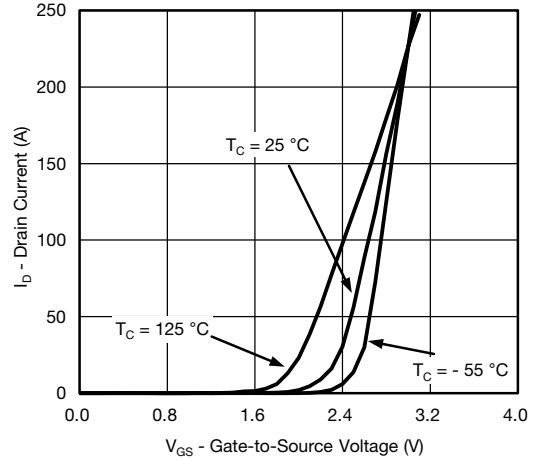
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



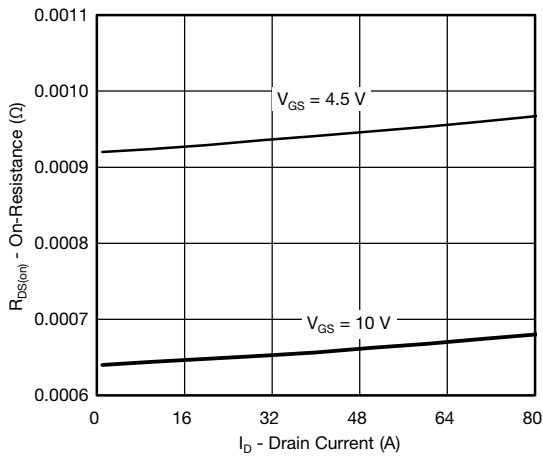
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



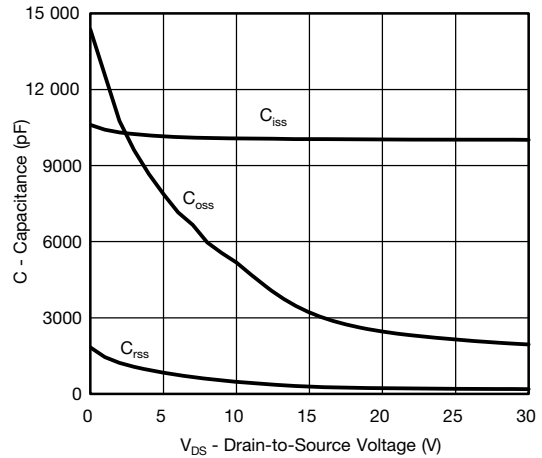
Output Characteristics



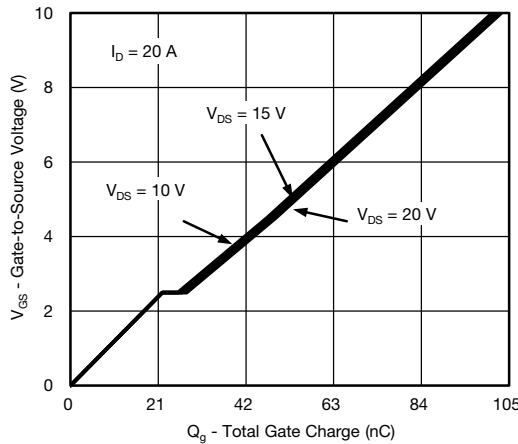
Transfer Characteristics



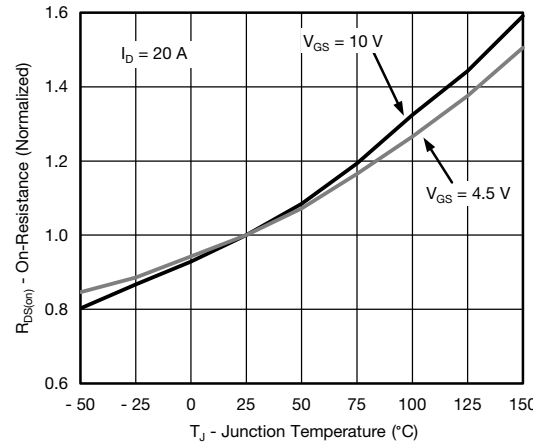
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



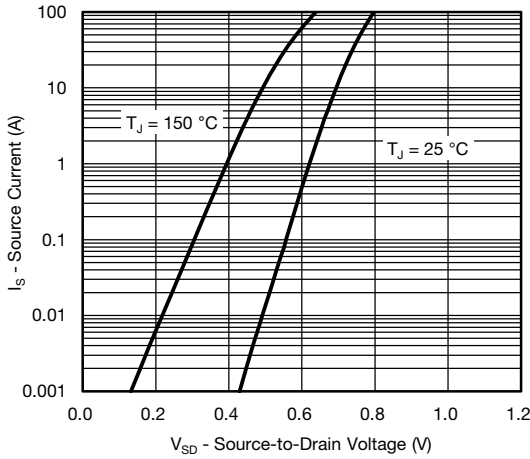
Gate Charge



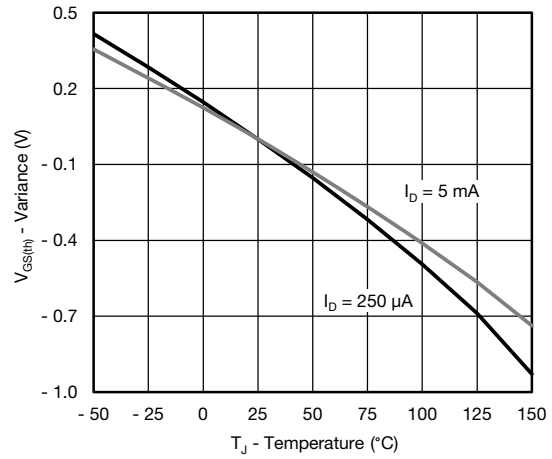
On-Resistance vs. Junction Temperature



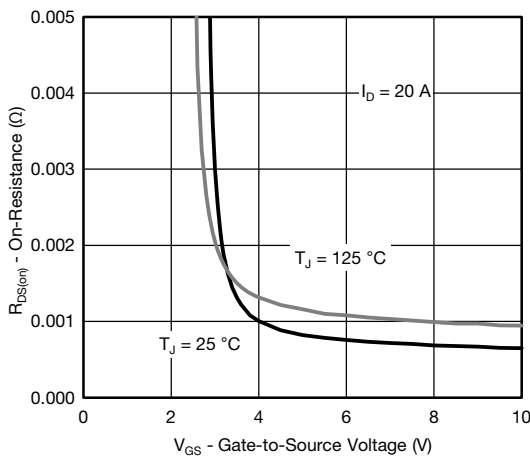
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



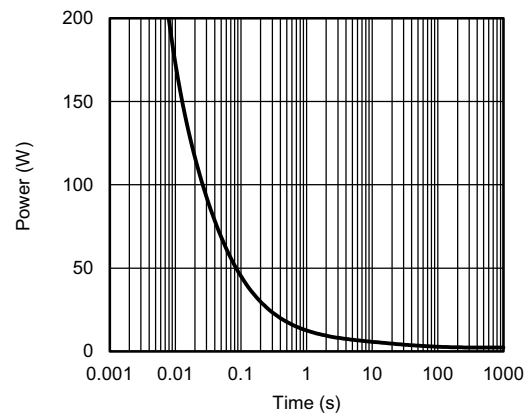
Source-Drain Diode Forward Voltage



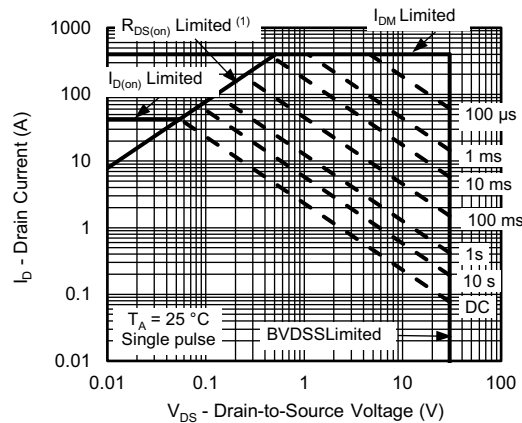
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage



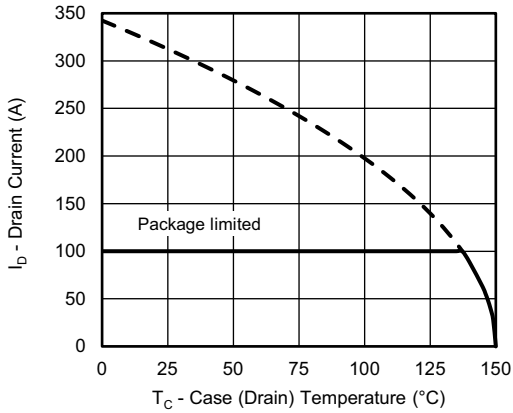
Single Pulse Power, Junction-to-Ambient



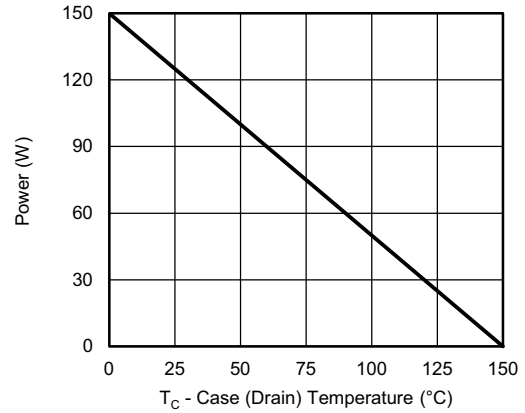
Safe Operating Area, Junction-to-Ambient



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



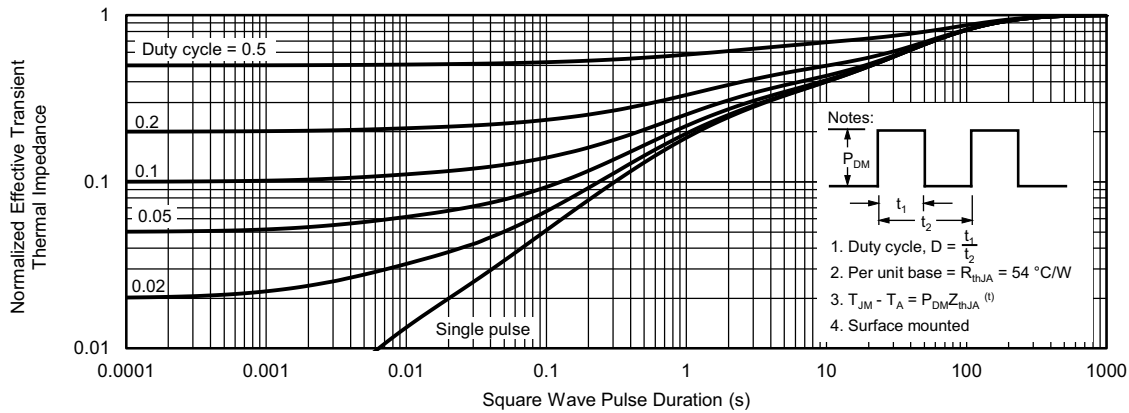
Current Derating ^a



Power, Junction-to-Case

Note

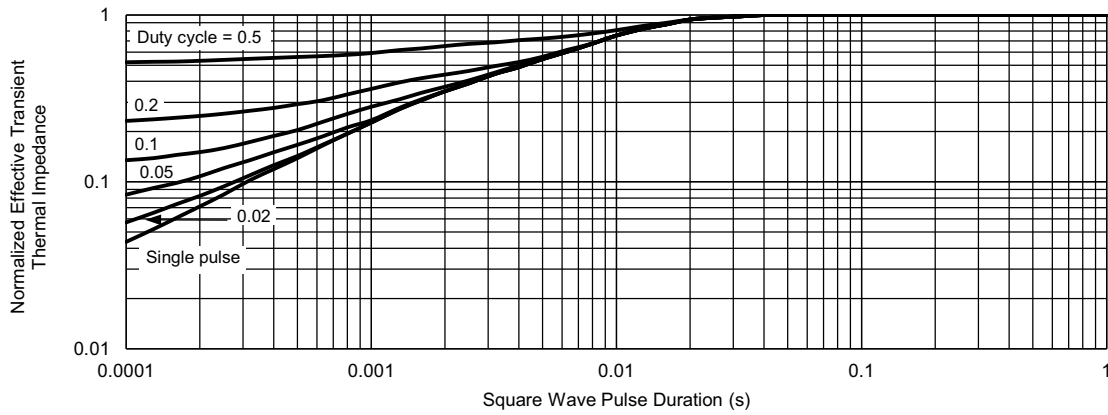
a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



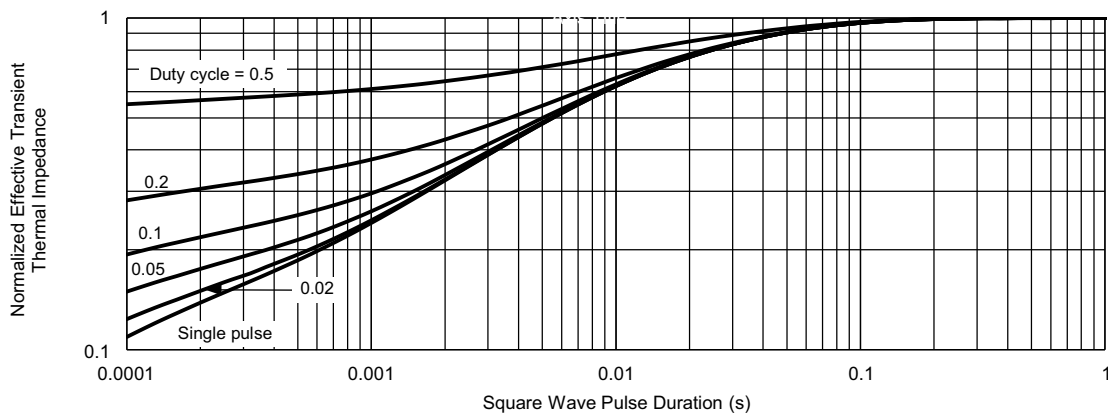
Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case (Drain)

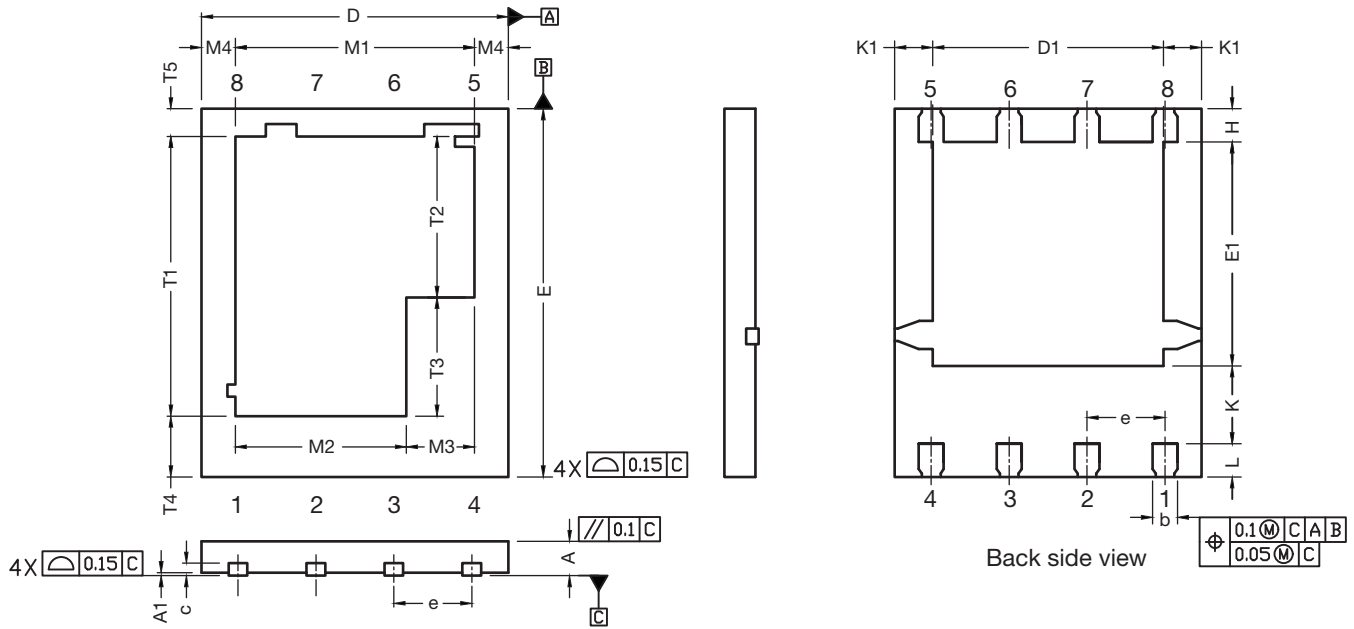


Normalized Thermal Transient Impedance, Junction-to-Case (Source)

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PowerPAK[®] SO-8 Double Cooling Case Outline



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.51	0.56	0.61	0.012	0.014	0.016
A1	0.00	0.02	0.05	0.000	0.0008	0.002
b	0.36	0.41	0.46	0.014	0.016	0.018
c	0.15	0.20	0.25	0.006	0.008	0.010
D	4.90	5.00	5.10	0.193	0.197	0.201
D1	3.71	3.76	3.81	0.146	0.148	0.150
e	1.27 BSC			0.050 BSC		
E	5.90	6.00	6.10	0.232	0.236	0.240
E1	3.60	3.65	3.70	0.142	0.144	0.146
H	0.49	0.54	0.59	0.019	0.021	0.023
K	1.22	1.27	1.32	0.048	0.050	0.052
K1	0.64 typ.			0.025 typ.		
L	0.49	0.54	0.59	0.019	0.021	0.023
M1	3.85	3.90	3.95	0.152	0.154	0.156
M2	2.74	2.79	2.84	0.108	0.110	0.112
M3	1.06	1.11	1.16	0.042	0.044	0.046
M4	0.56 typ.			0.022 typ.		
N	8			8		
T1	4.51	4.56	4.61	0.178	0.180	0.182
T2	2.58	2.63	2.68	0.102	0.104	0.106
T3	1.88	1.93	1.98	0.074	0.076	0.078
T4	0.97 typ.			0.038 typ.		
T5	0.48 typ.			0.019 typ.		

ECN: T16-0445-Rev. A, 11-Jul-16
DWG: 6048

RECOMMENDED MINIMUM PADS FOR PowerPAK® SO-8 Single



Recommended Minimum Pads
Dimensions in Inches/(mm)

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